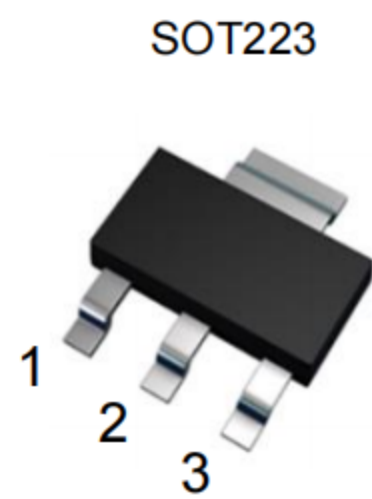


Features

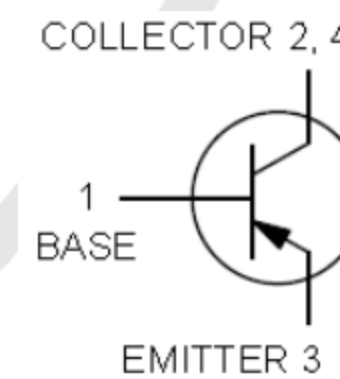
- High Collector Current
- Low Collector-emitter Saturation Voltage

Mechanical Data

- Case: SOT-223
- Molding compound, UL flammability classification rating 94V-0
- Terminals: Matte tin plated leads, solderable per MIL-STD-202, Method 208



Circuit Diagram



Marking:BCP52-16

Absolute Maximum Ratings (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	TPBCP52-16	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current (Continuous)	I _C	-1	A
Collector Current (Peak)	I _{CM}	-1.5	A

Thermal Characteristic

Parameter	Symbol	Value	Unit
Power Dissipation ($T_A = 25^{\circ}\text{C}$) * ¹	P_D	1.5	W
Thermal Resistance Junction-to-Air * ²	$R_{\theta JA}$	104	$^{\circ}\text{C/W}$
Thermal Resistance Junction-to-Case * ²	$R_{\theta JC}$	32	$^{\circ}\text{C/W}$
Thermal Resistance Junction-to-Lead * ²	$R_{\theta JL}$	14	$^{\circ}\text{C/W}$
Operating junction Temperature	T_J	-55 ~ +150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-60	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-60	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30\text{V}, I_E = 0$	-	-	-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -5\text{mA}$	25	-	-	-
		$V_{CE} = -2\text{V}, I_C = -150\text{mA}$	100	-	250	-
		$V_{CE} = -2\text{V}, I_C = -500\text{mA}$	25	-	-	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$	-	-	-0.5	V
Base-Emitter Voltage	$V_{BE(on)}$	$I_C = -500\text{mA}, V_{CE} = -2\text{V}$	-	-	-1	V
Transition Frequency	f_T	$V_{CE} = -10\text{V}, I_C = -50\text{mA}$ $f = 20\text{MHz}$	-	125	-	MHz



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TPBCP52-16

PNP Silicon Epitaxial Planar Transistor

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Typical Electrical Characteristic Curves

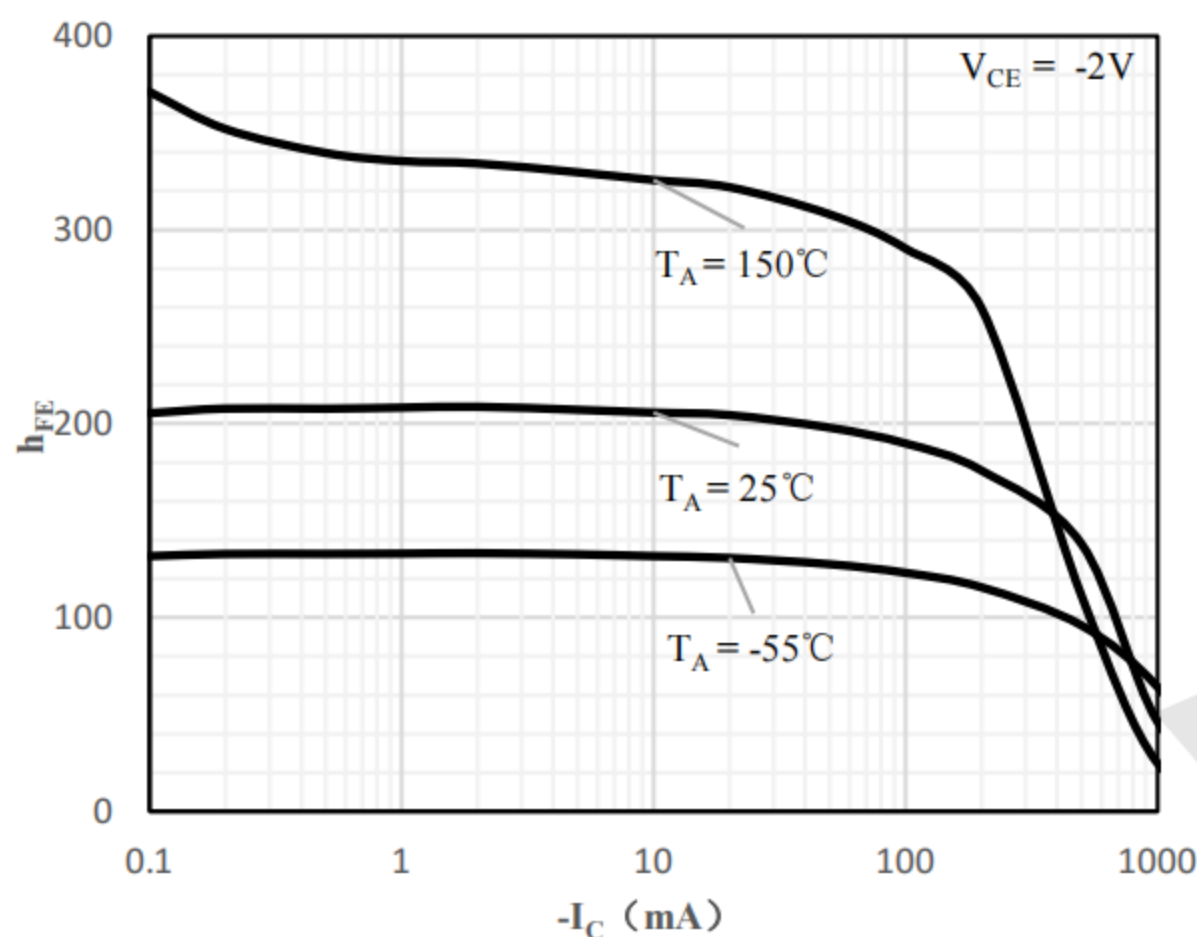


Fig 1 h_{FE} vs. I_C (BCP51/52/53-16)

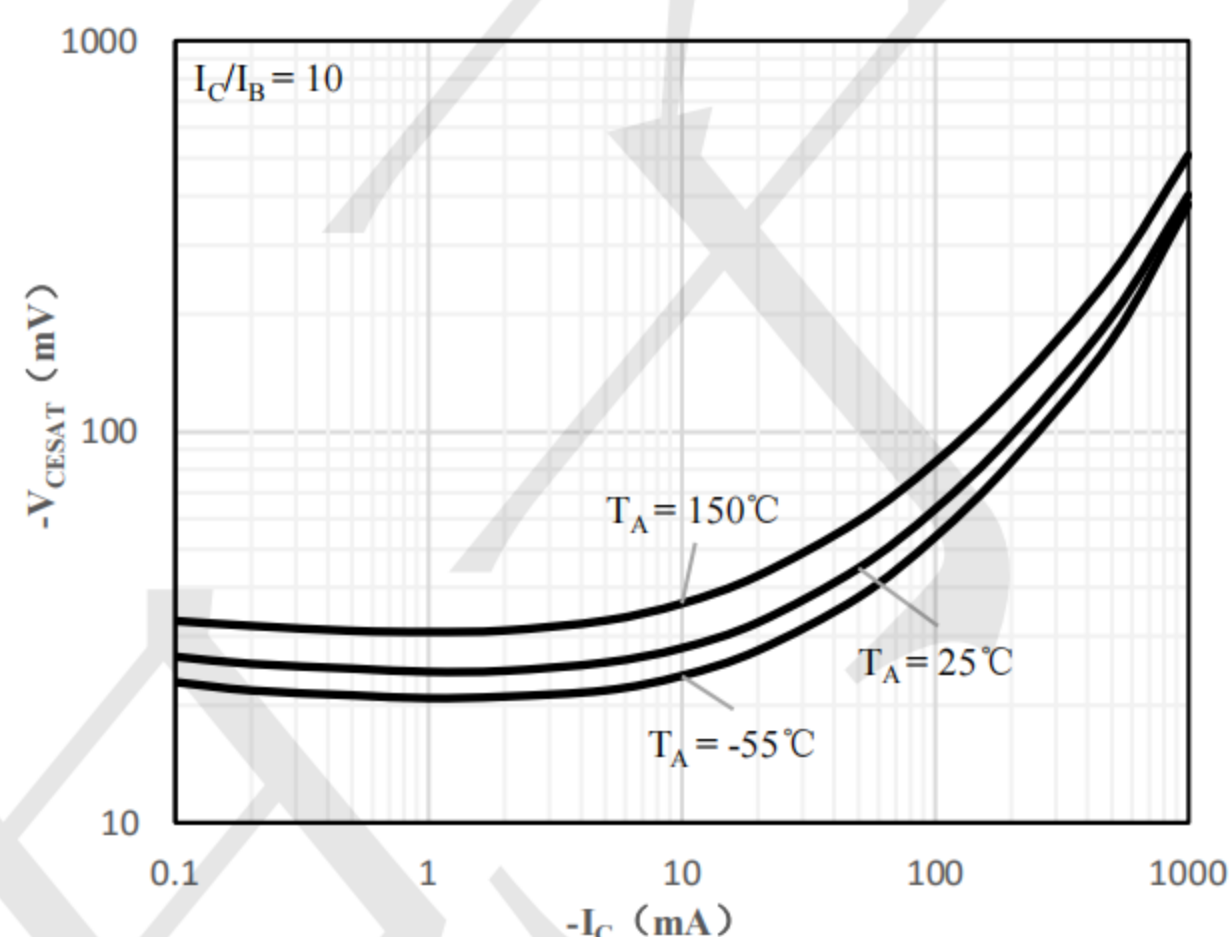


Fig 2 $V_{CE(sat)}$ vs. I_C

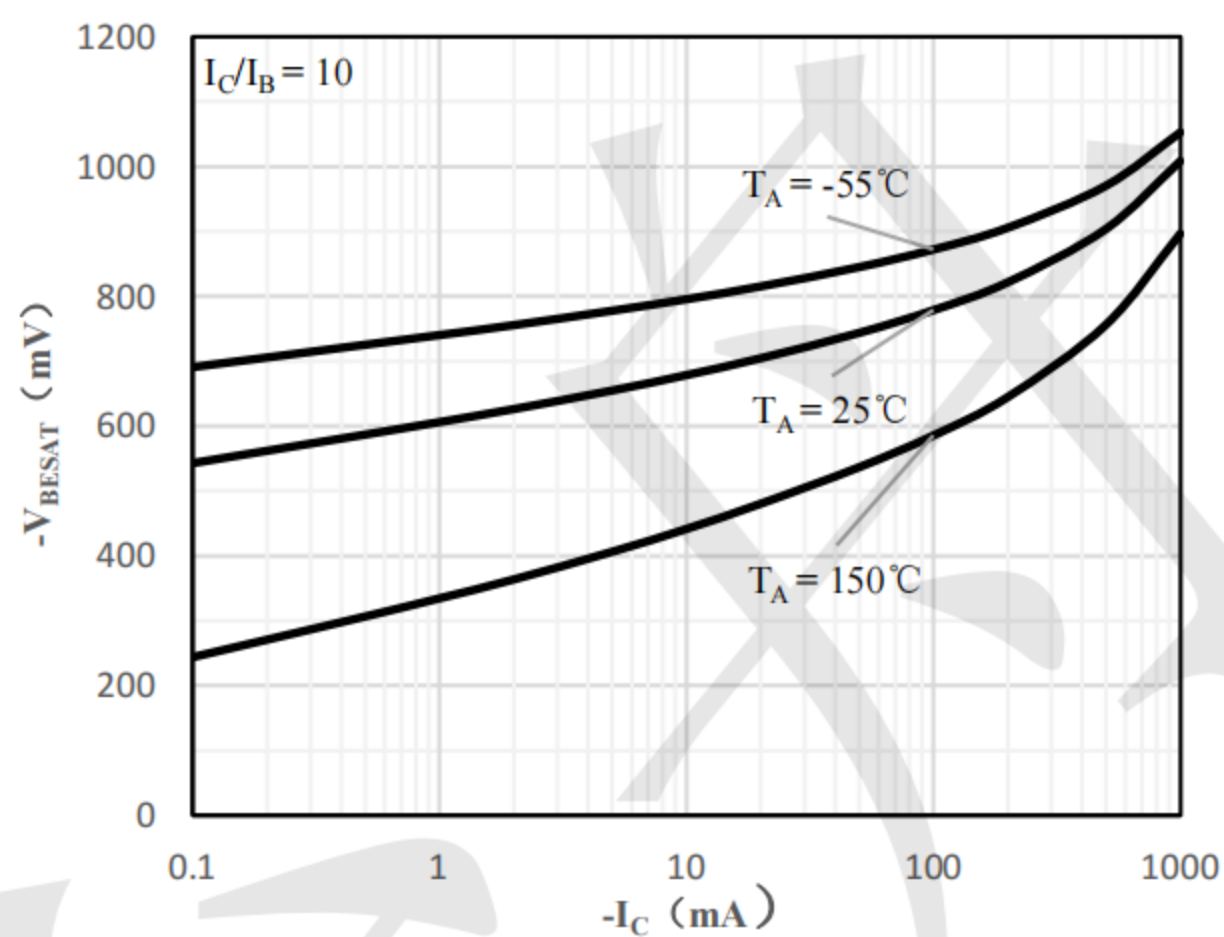


Fig 3 $V_{BE(sat)}$ vs. I_C

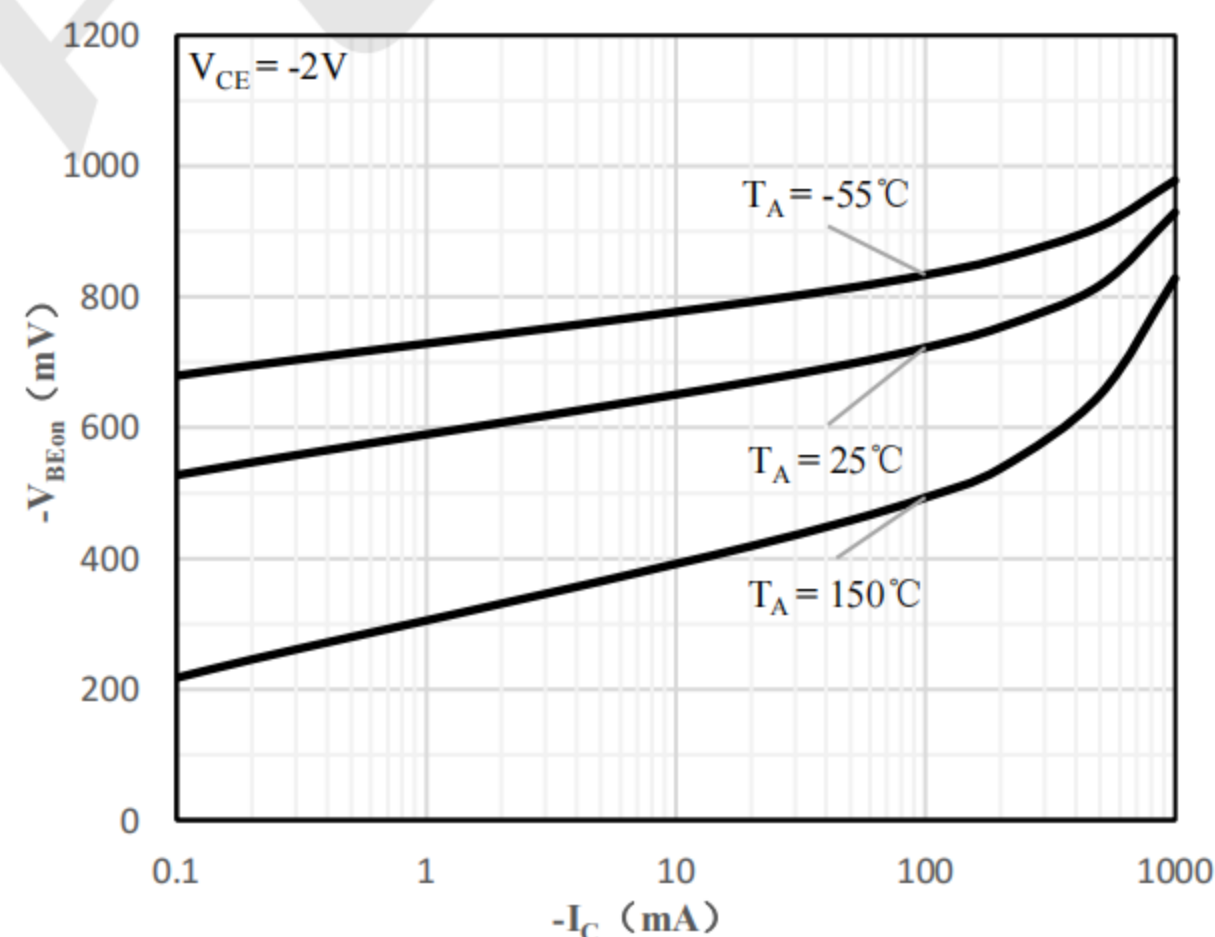


Fig 4 $V_{BE(on)}$ vs. I_C

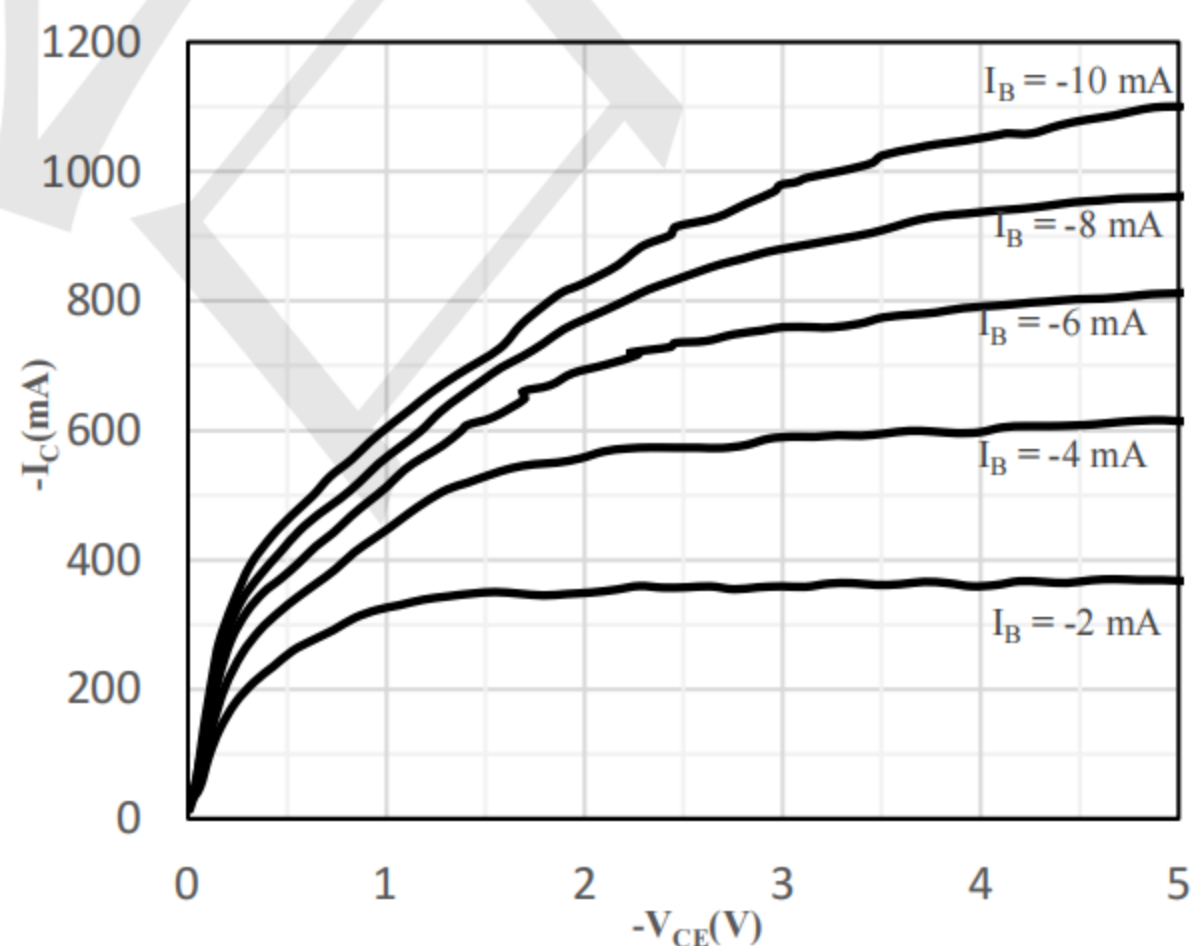


Fig 5 I_C vs. V_{CE}

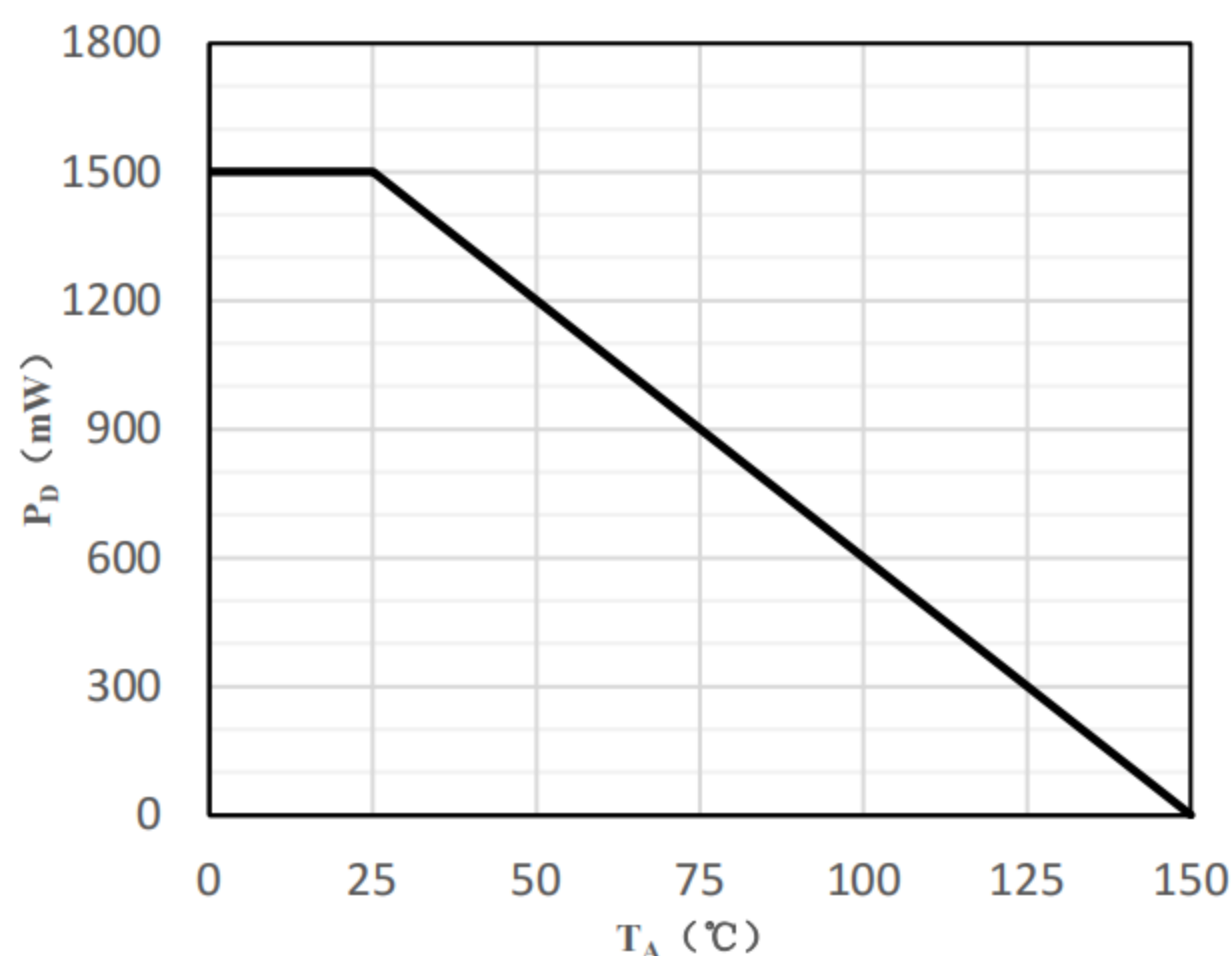


Fig 6 P_D vs. T_A



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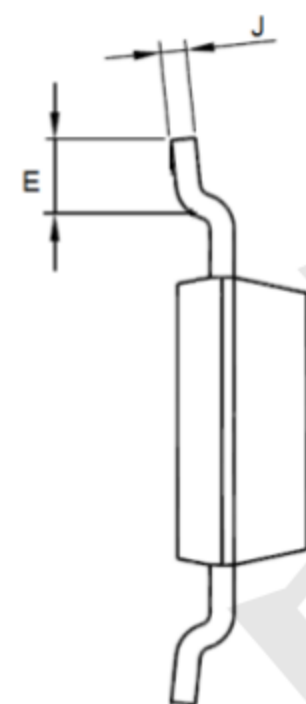
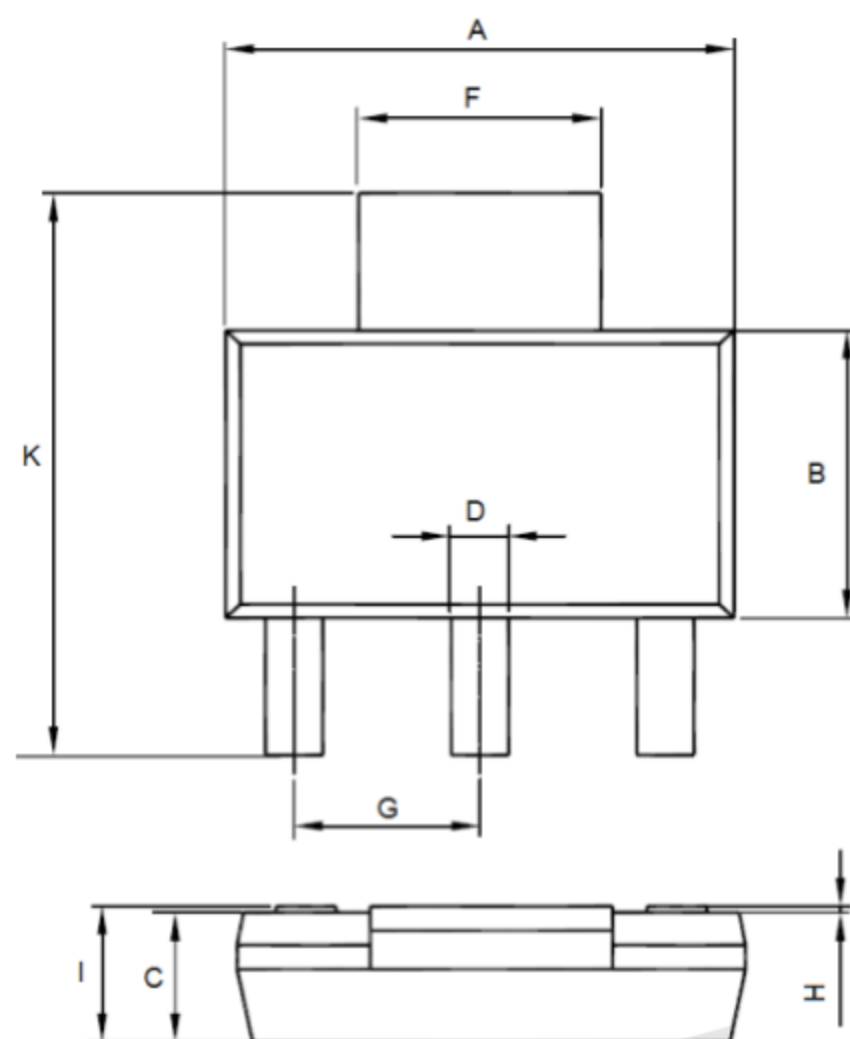
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Outline Drawing - SOT223



SOT-223		
Dim	Min	Max
A	6.10	6.50
B	3.30	3.70
C	1.50	1.70
D	0.66	0.82
E	0.90	1.15
F	2.90	3.10
G	2.20	2.40
H	0.02	0.10
I	1.52	1.80
J	0.20	0.40
K	6.70	7.30

